

FIG. 1 (prior art)

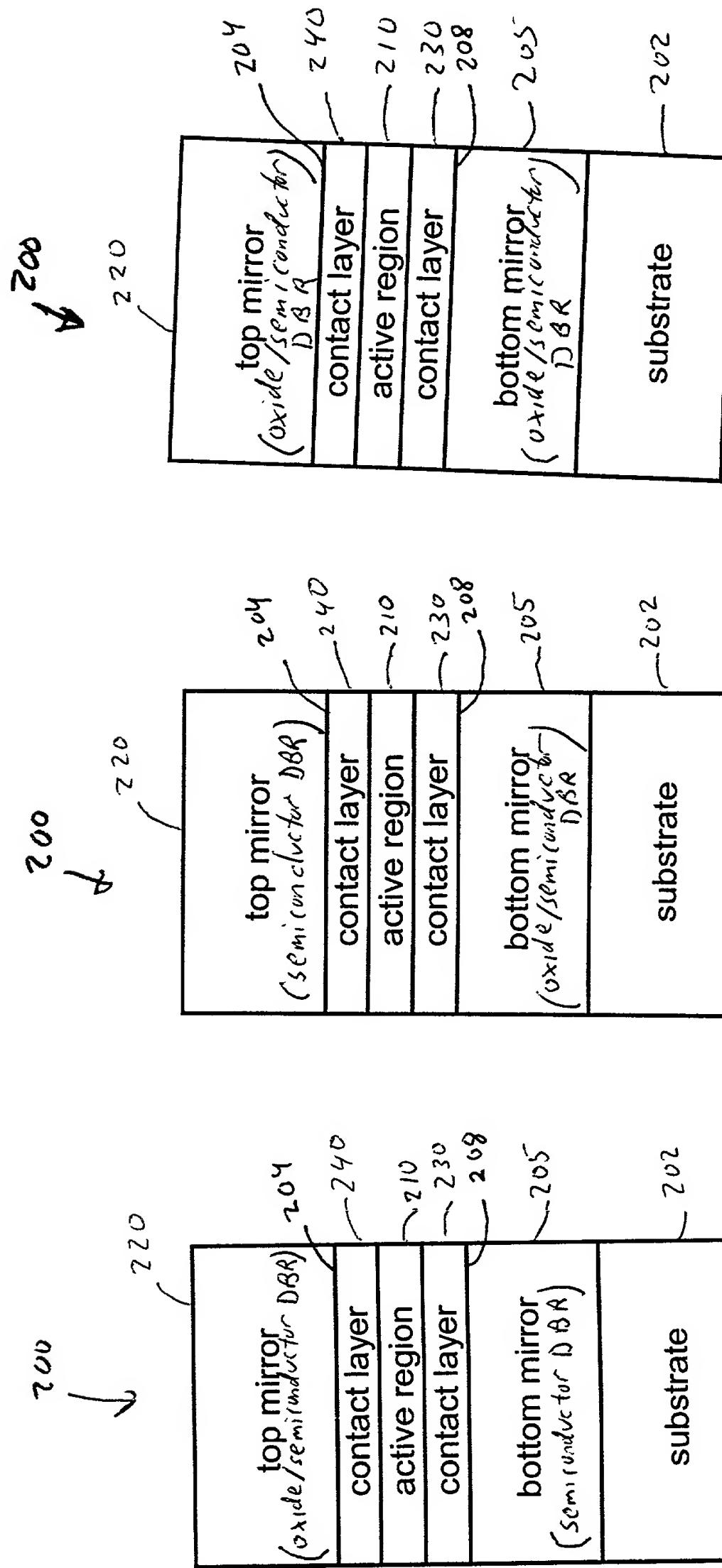


FIG 6. 2C

FIG 6. 2B

FIG 6. 2A

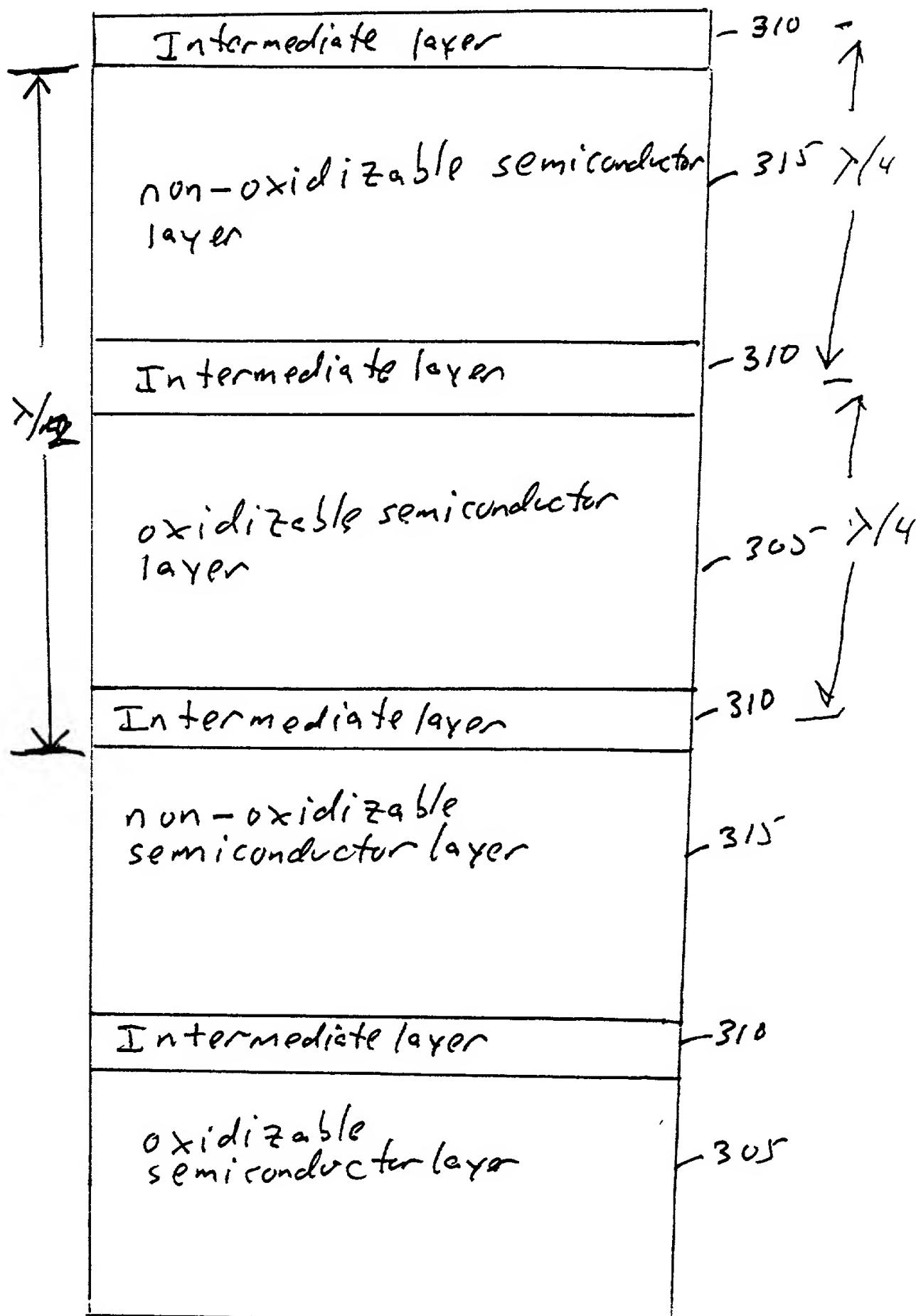


FIG. 3

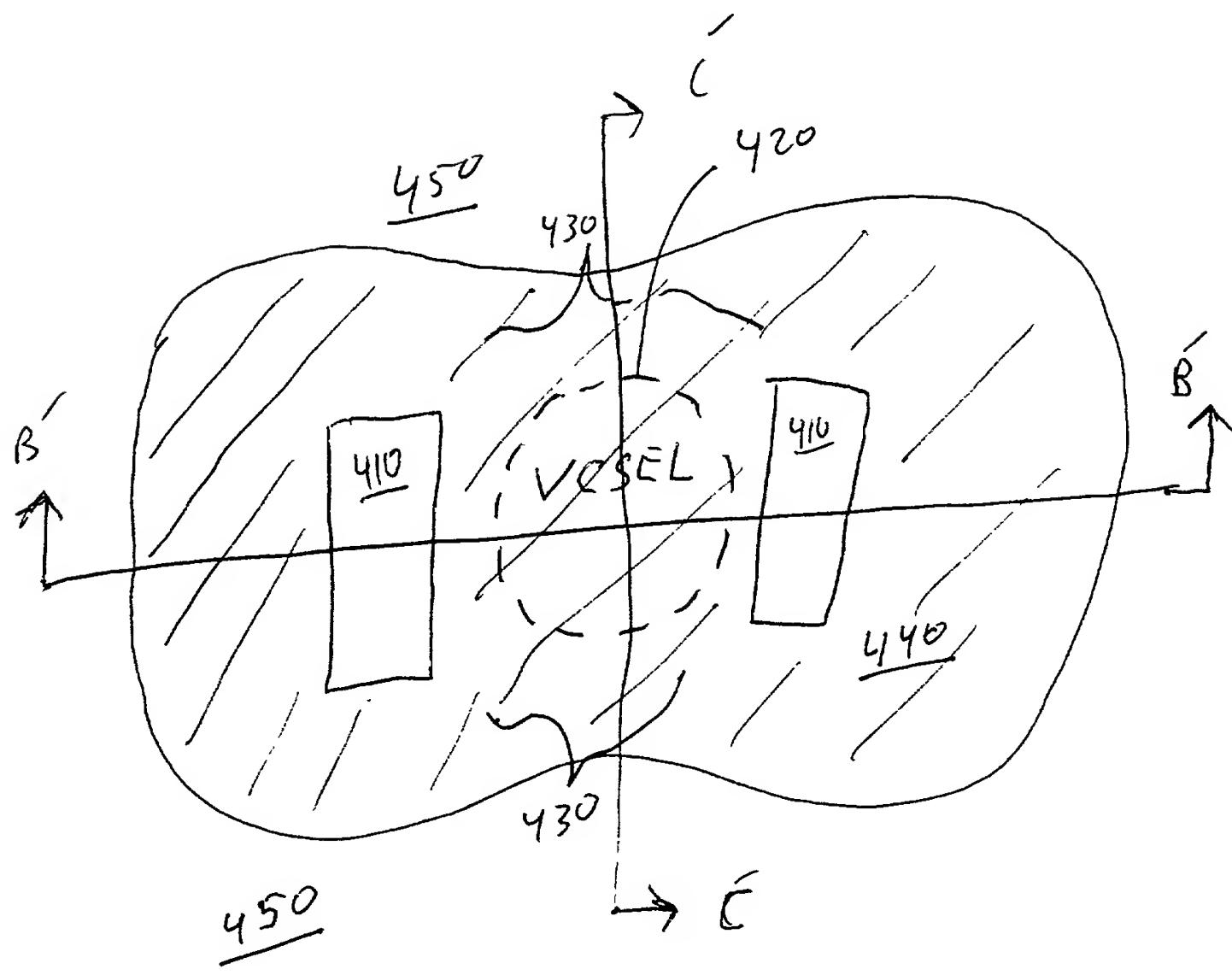
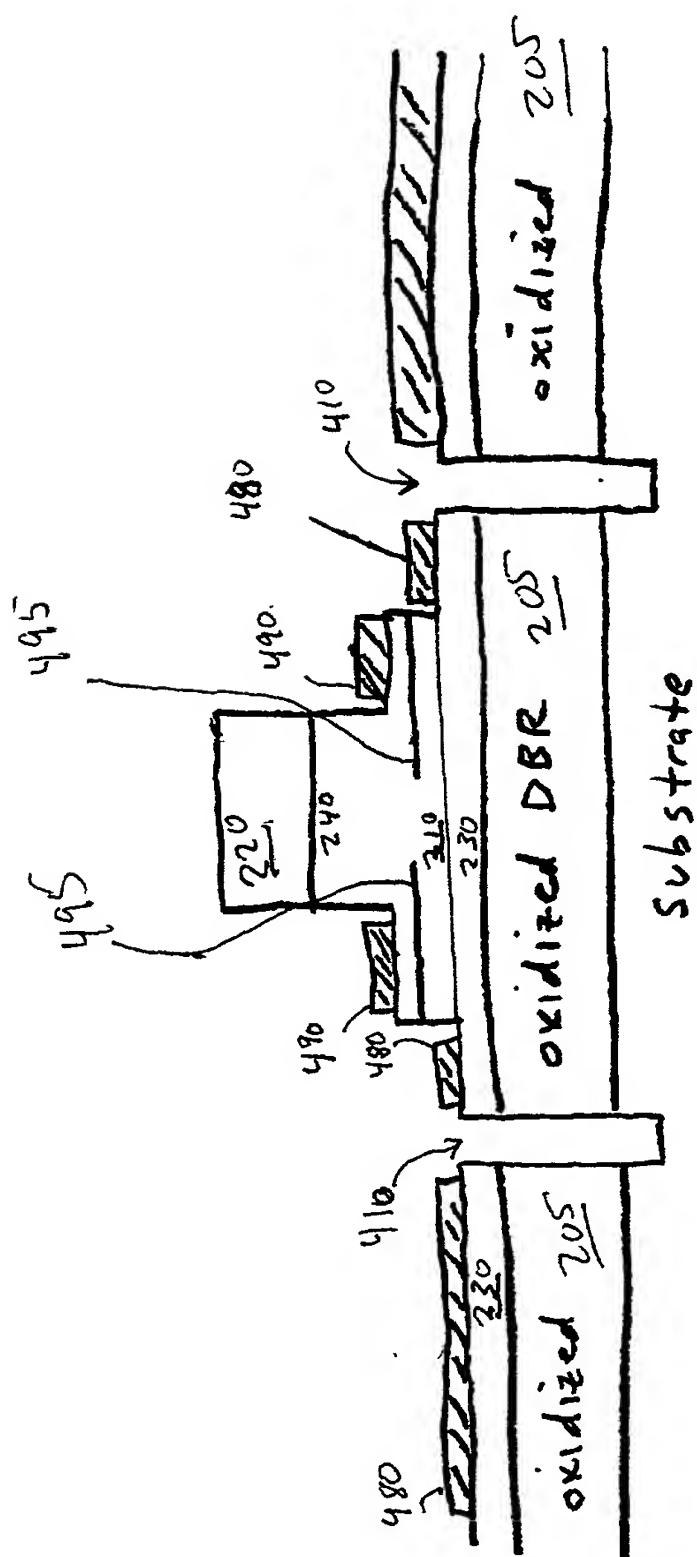


FIG. 4A



F 176. 48

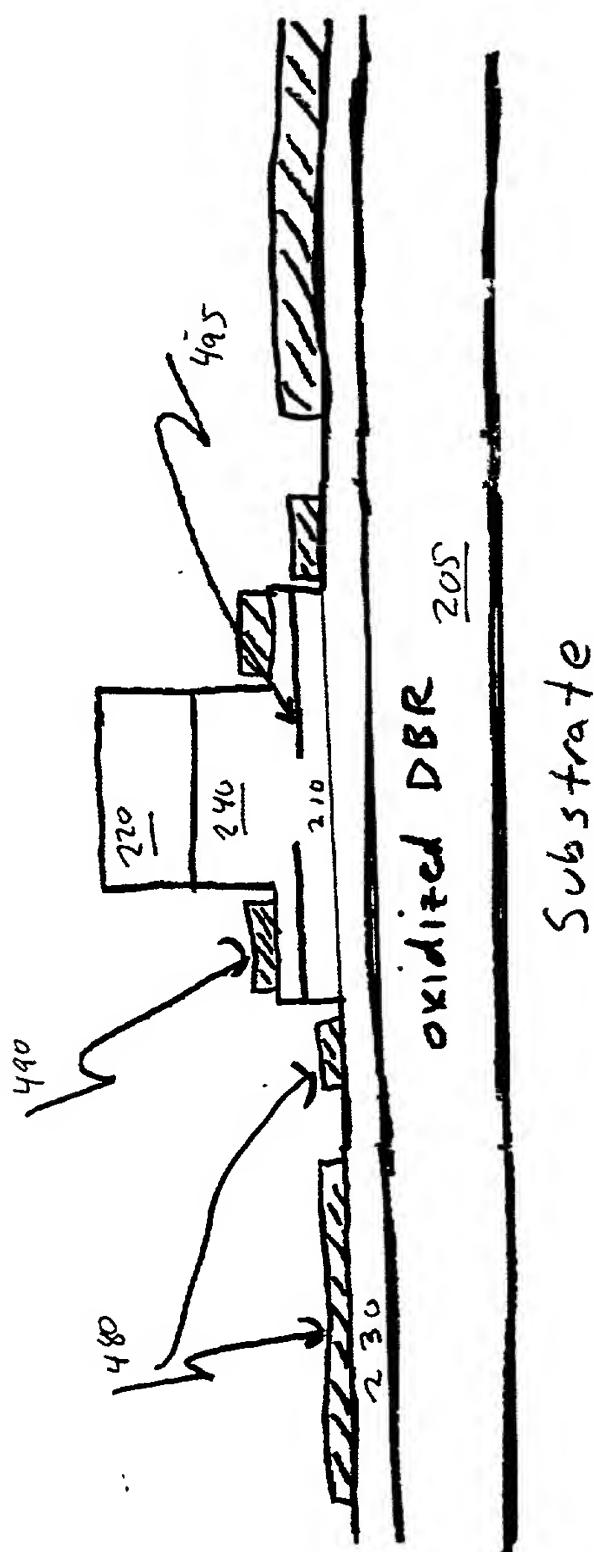


FIG. 4C

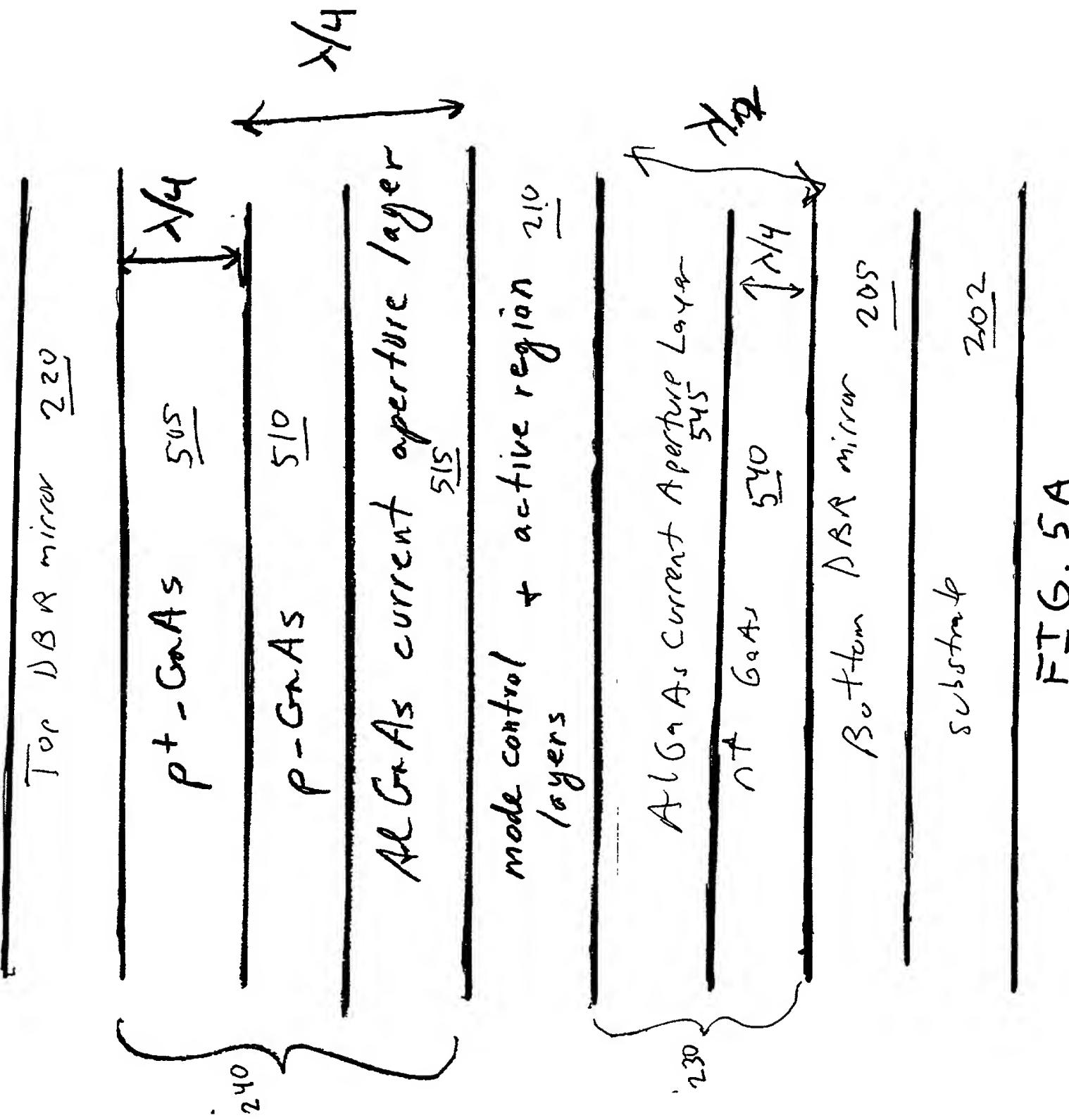
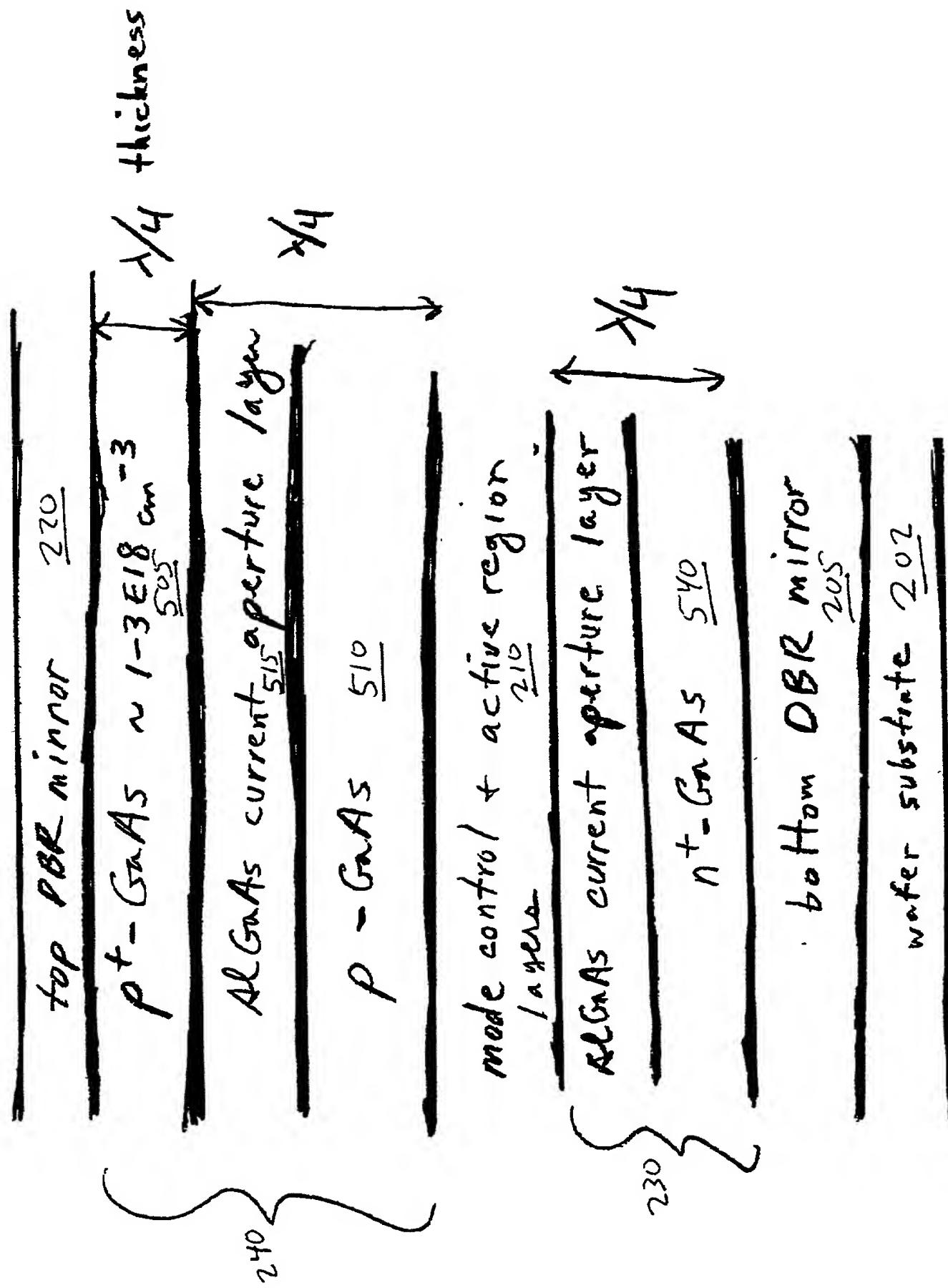


FIG. 5A



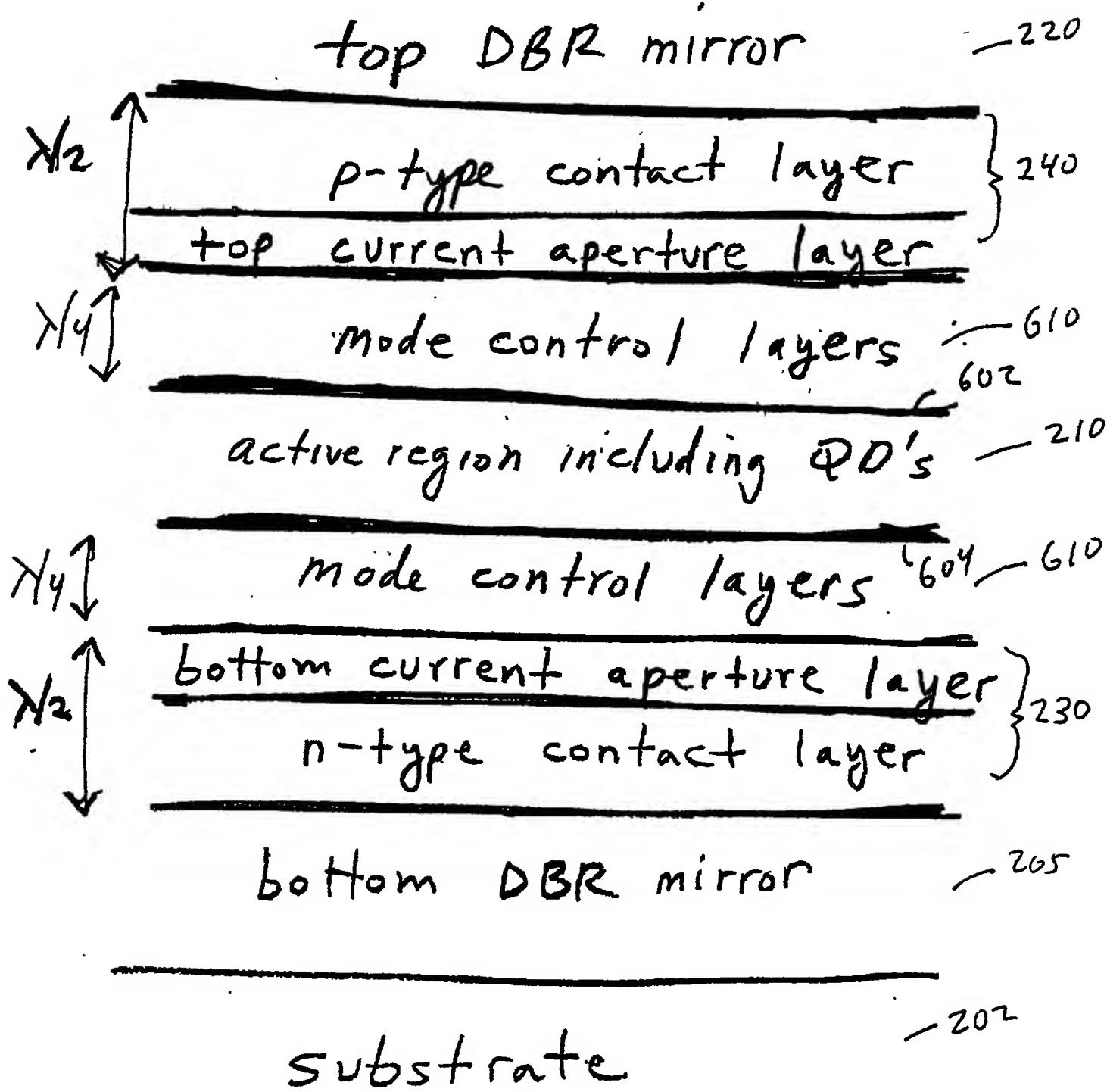


FIG. 6A

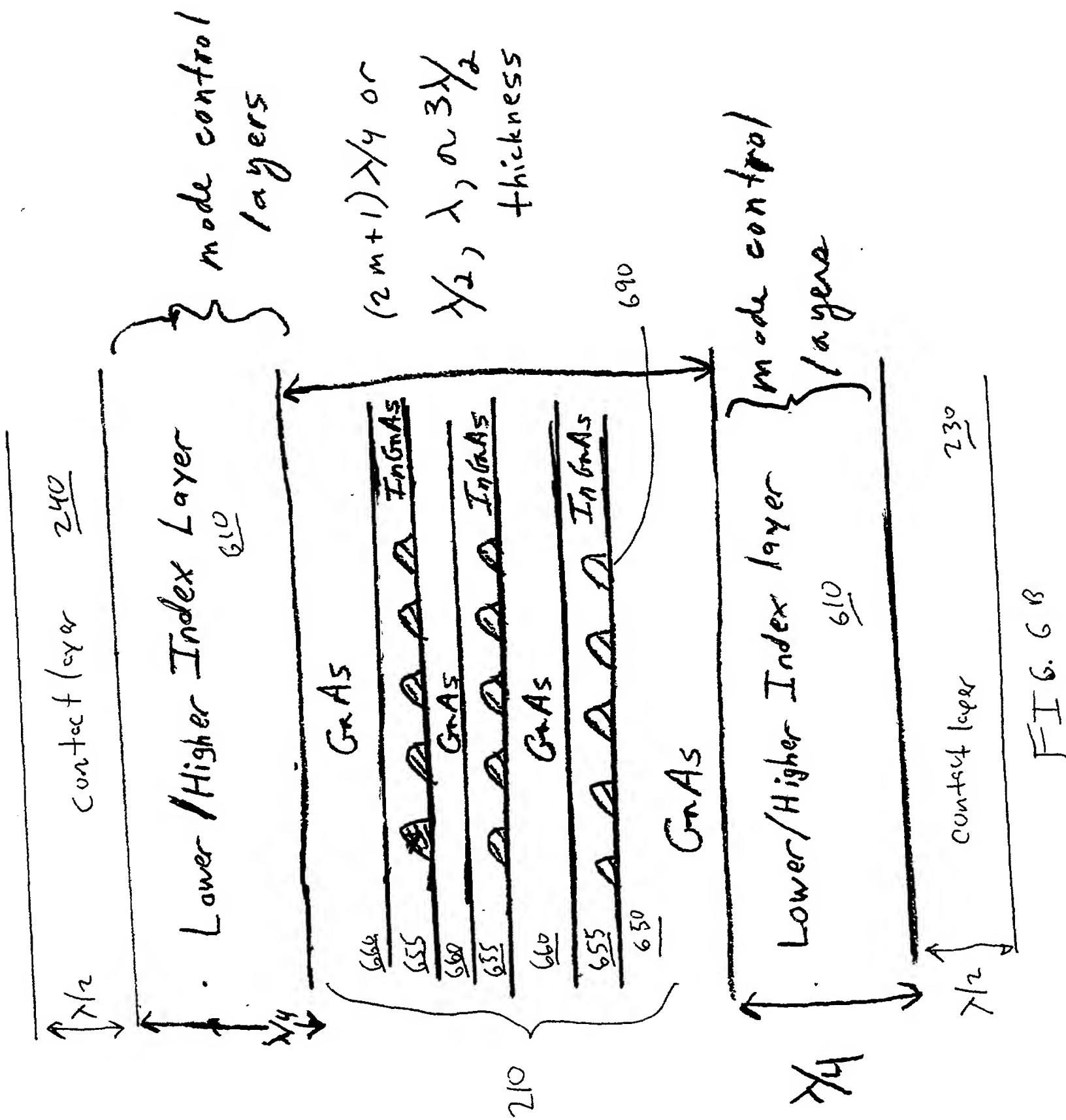


FIG. 6 B

✓ 200

120	GaAs	92nm, 5x	
	Al _{0.92} Ga _{0.08} As	10nm, 5x	
	AlAs	213nm, 5x	
	Al _{0.92} Ga _{0.08} As	10nm, 5x	
240	GaAs, p3 ₁₈	92nm	p-contact
	Al _{0.92} Ga _{0.08} As, p1 ₁₇	p16/107nm	Mode Control
	GaAs, p1 ₁₇	71nm	p-contact
	Al _{0.98} Ga _{0.02} As, p1 ₁₆	p16/50nm	Current aperture
	Al _{0.92} Ga _{0.08} As	12nm	grade for current aperture
	GaAs	20nm	Active
	GaAs	10nm, 3x	600C Active
	GaAs	0.8nm, 3x	Active
210	In _{0.15} Ga _{0.85} As	~8nm, 3x	Active
	InAs	2.4ML, 3x	Active
	In _{0.15} Ga _{0.85} As	1nm, 3x	510C Active
	GaAs	159nm	Active
230	Al _{0.92} Ga _{0.08} As, n2 ₁₈	n16/107nm	Mode Control
	GaAs, n2 ₁₈	92nm	n-contact
	Al _{0.92} Ga _{0.08} As	10nm, 8x	
	AlAs	213nm, 8x	
205	Al _{0.92} Ga _{0.08} As	10nm, 8x	
	GaAs	92nm, 8x	
	Al _{0.92} Ga _{0.08} As	10nm	
	AlAs	213nm	
	Al _{0.92} Ga _{0.08} As	10nm	
	GaAs	200nm	600C
	GaAs N+ 2" 1-side	Tox=620C, 10min	

FIG 6.7

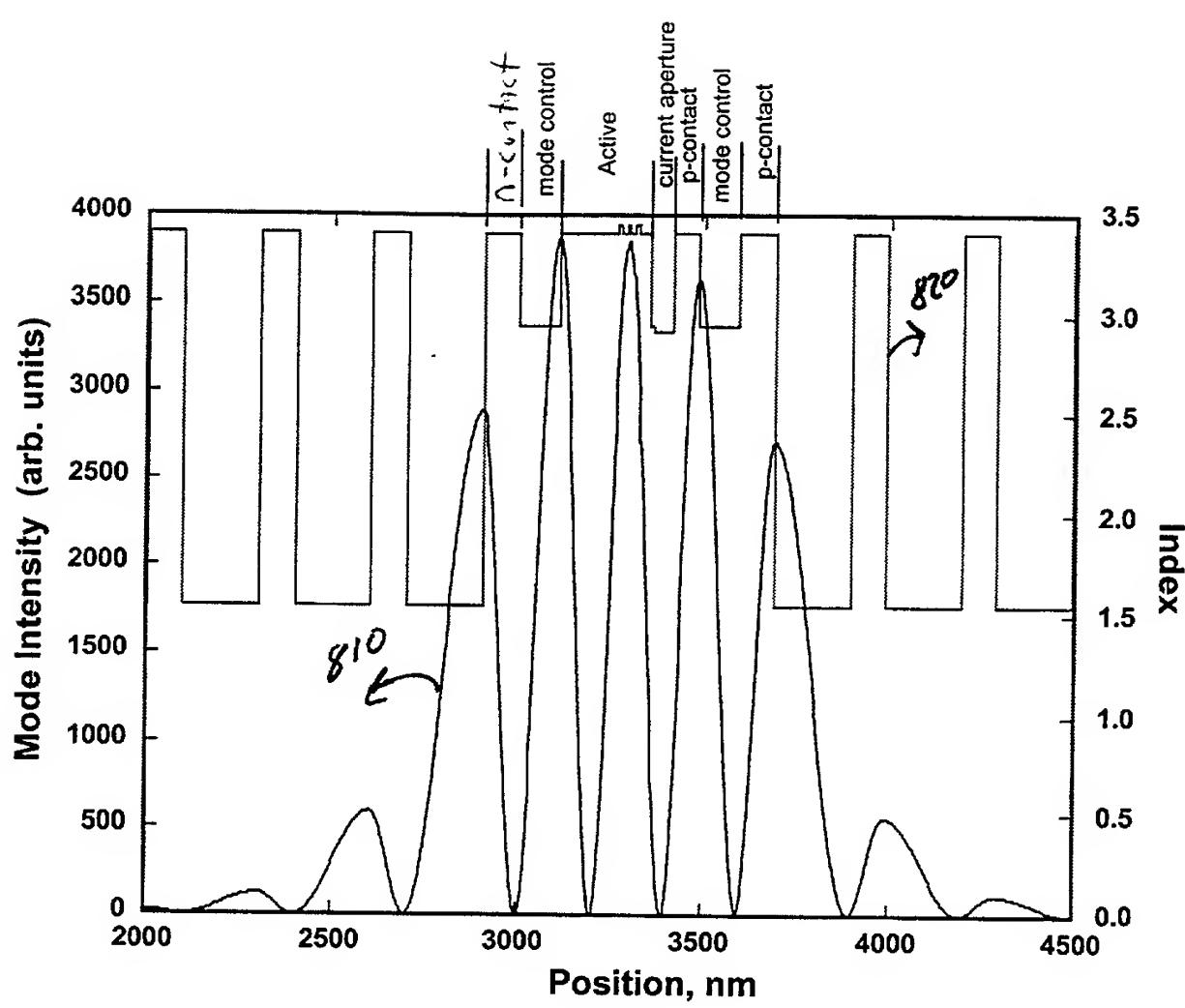


FIG. 8

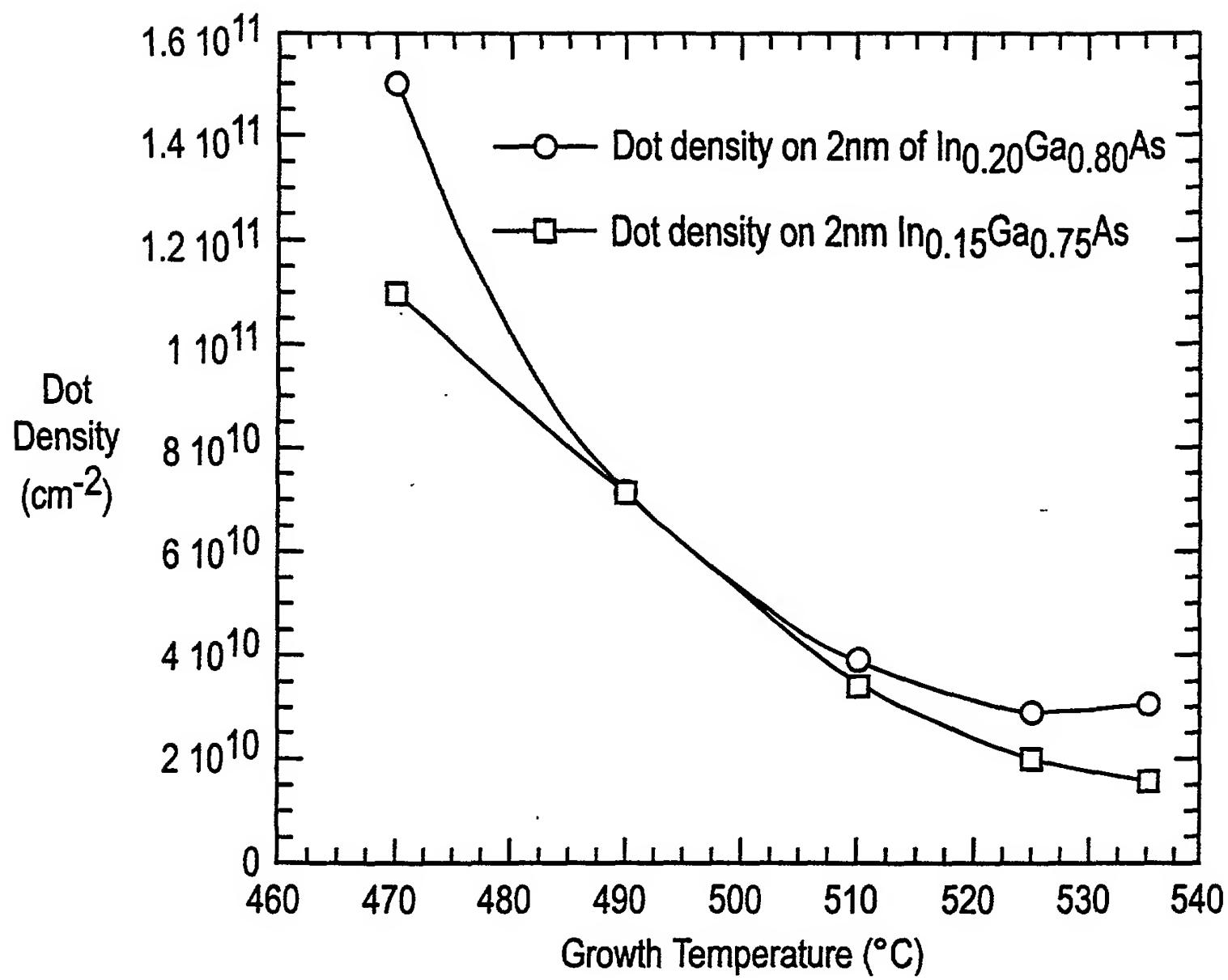


FIG. 9

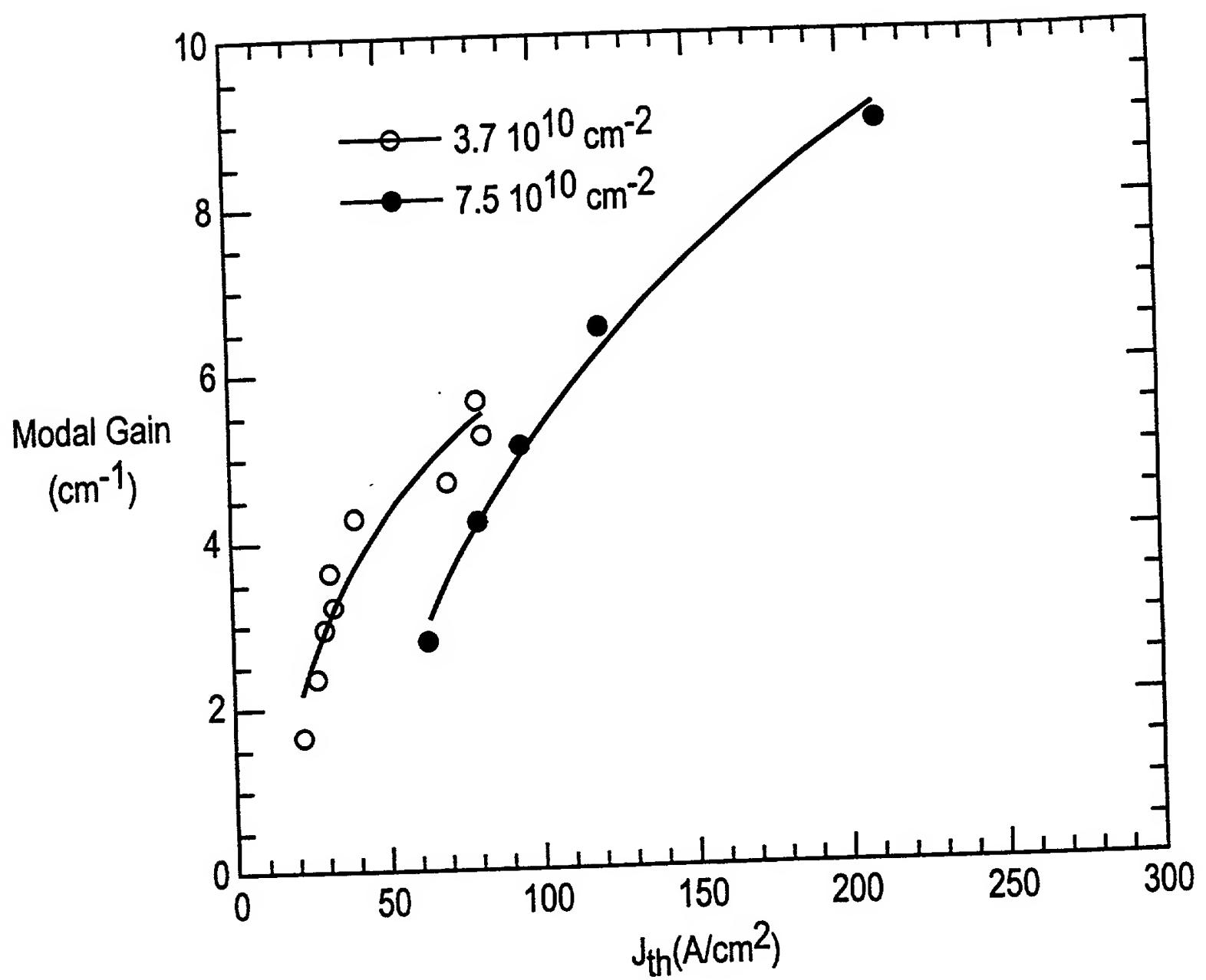


FIG. 10

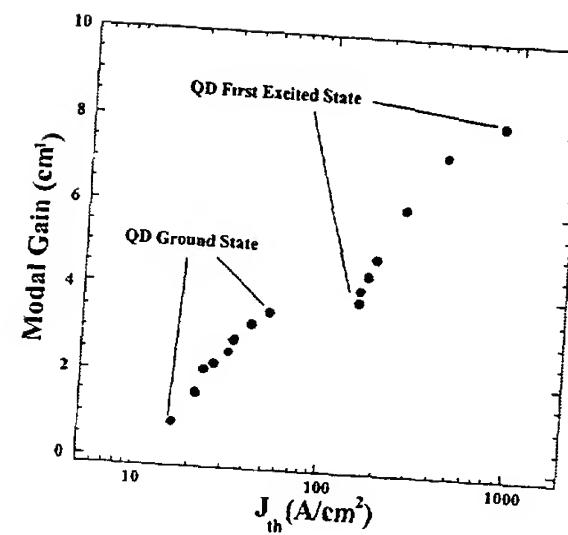


FIG. 11

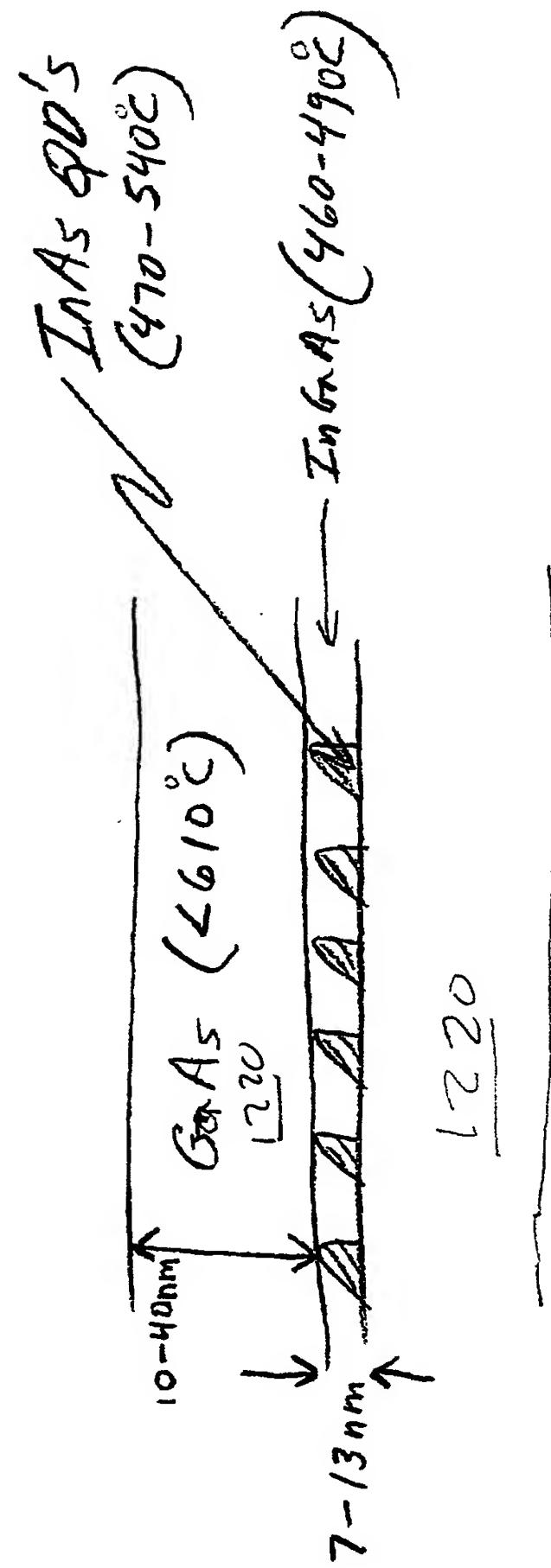


FIG. 12 A

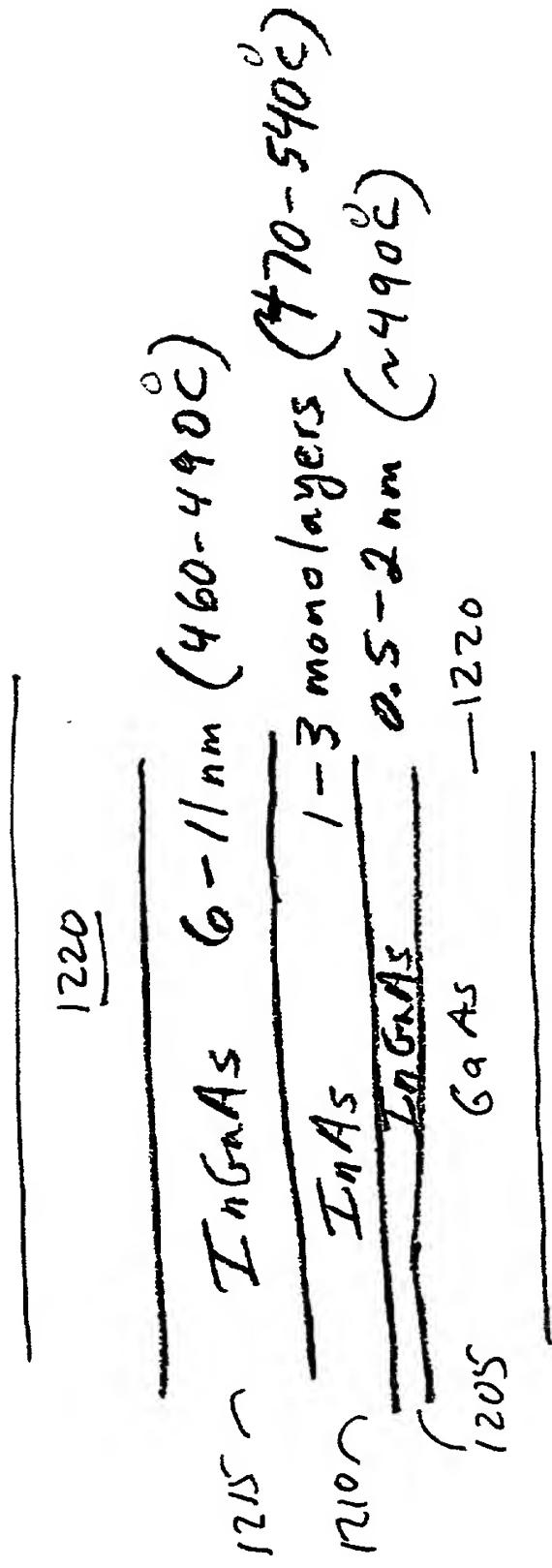


FIG. 12 B

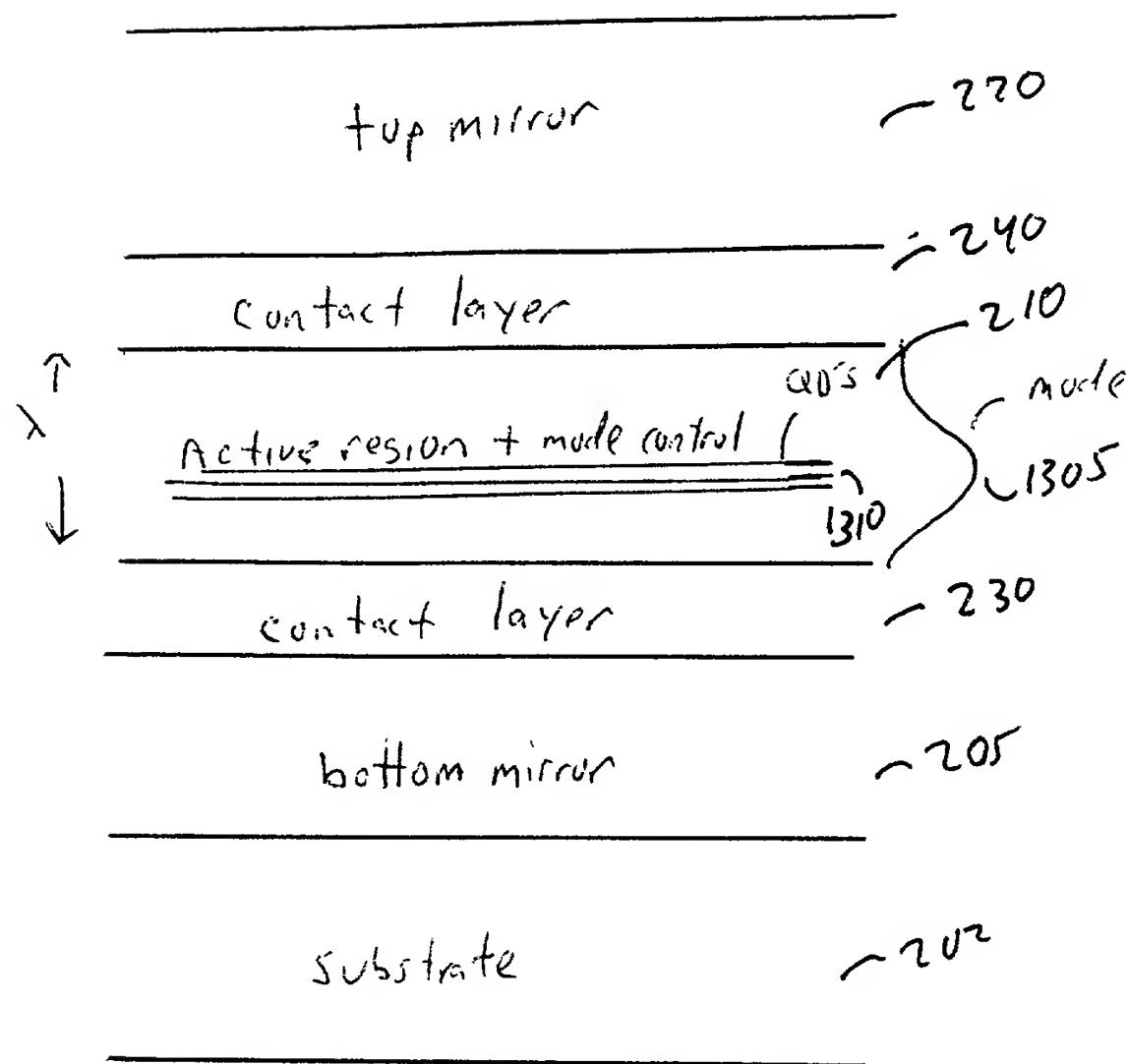


FIG. 13

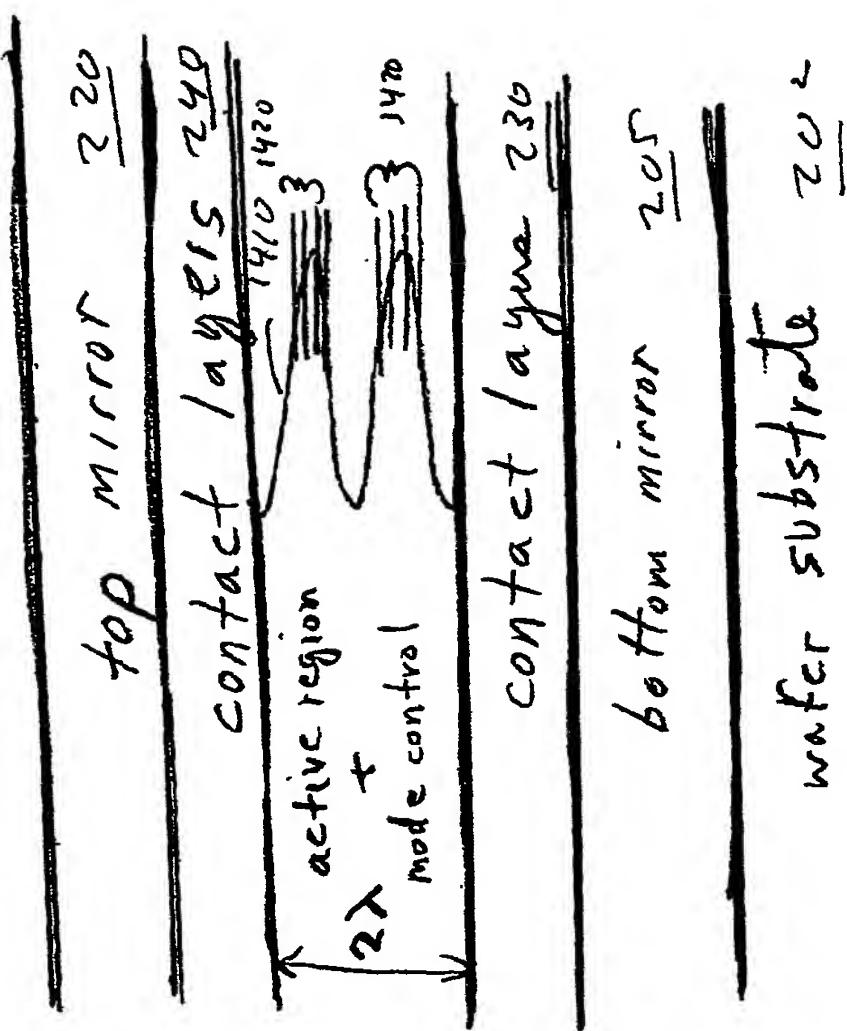


FIG. 14

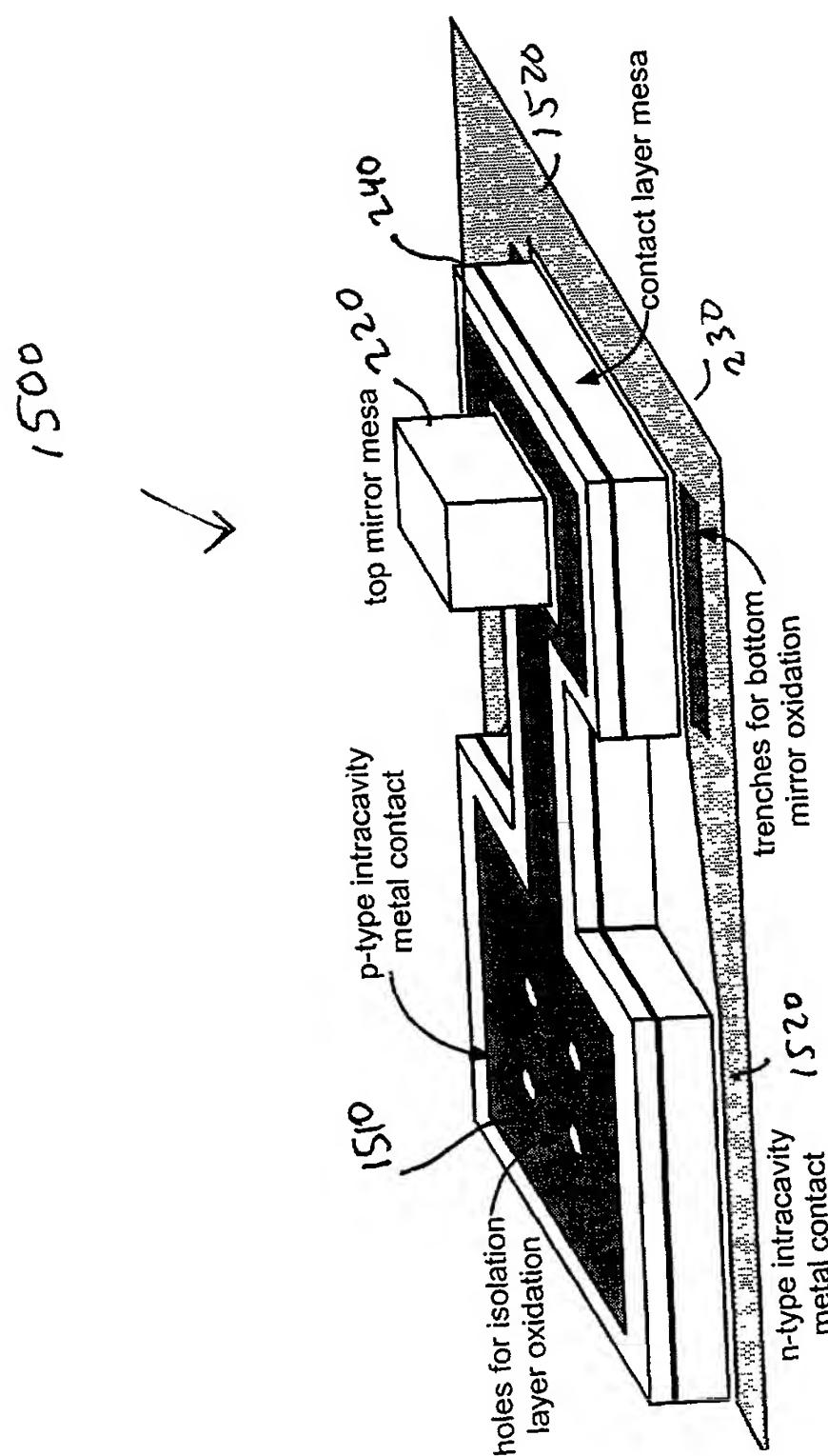


FIG. 15A

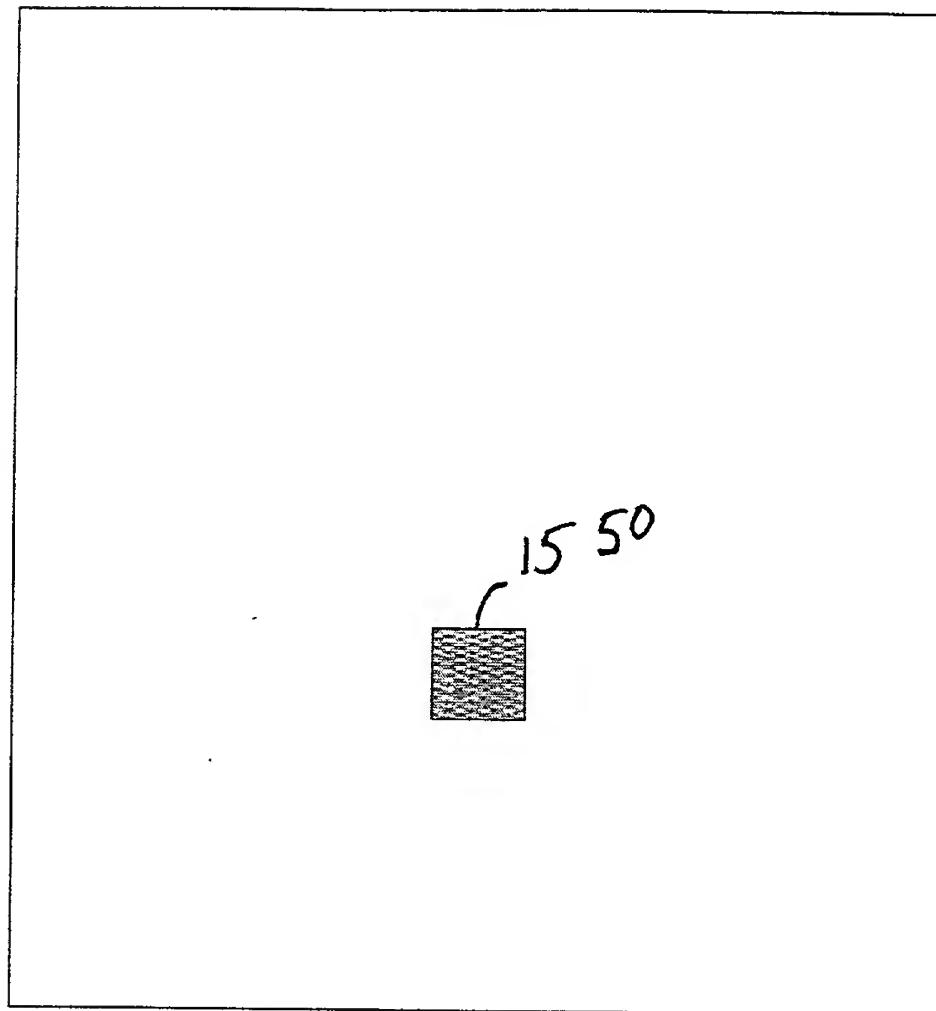


FIG. 15B

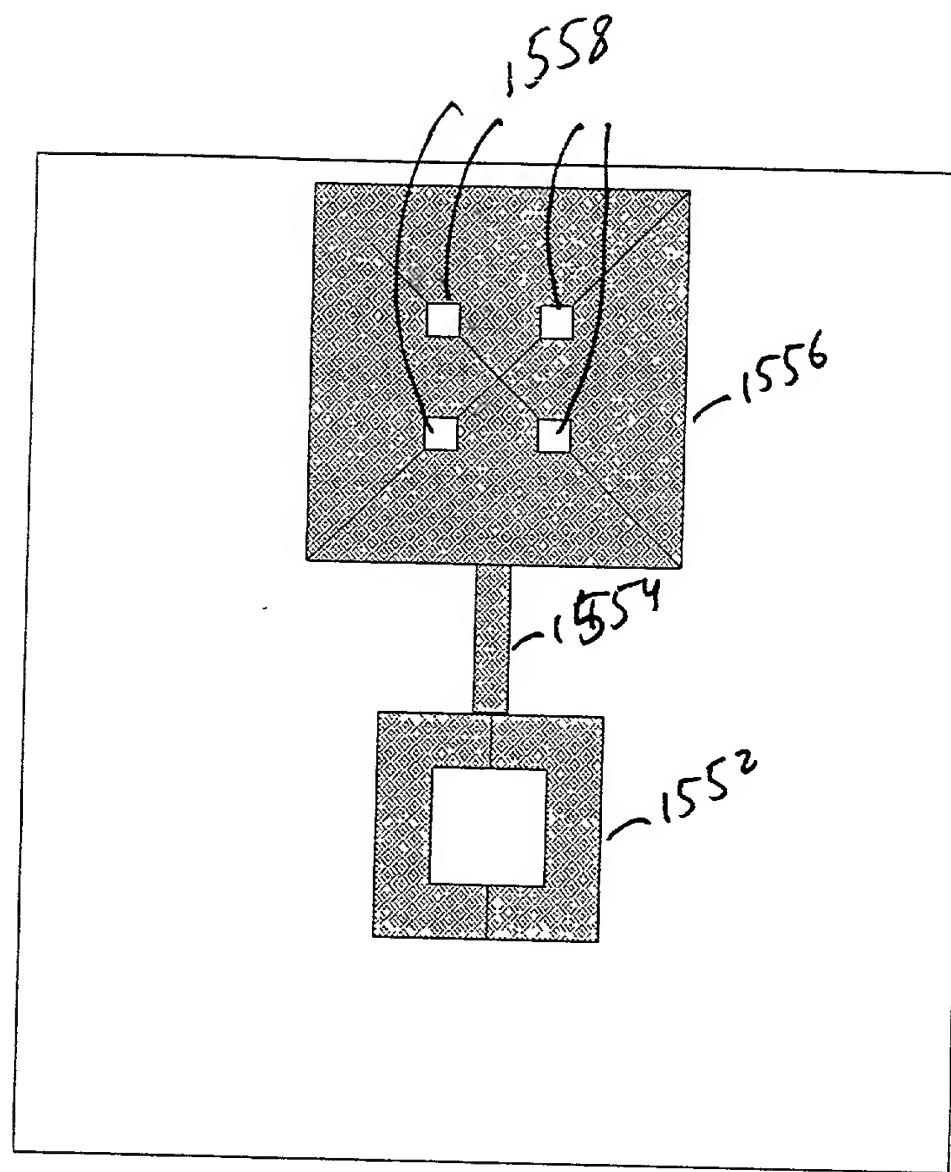


FIG. 15C

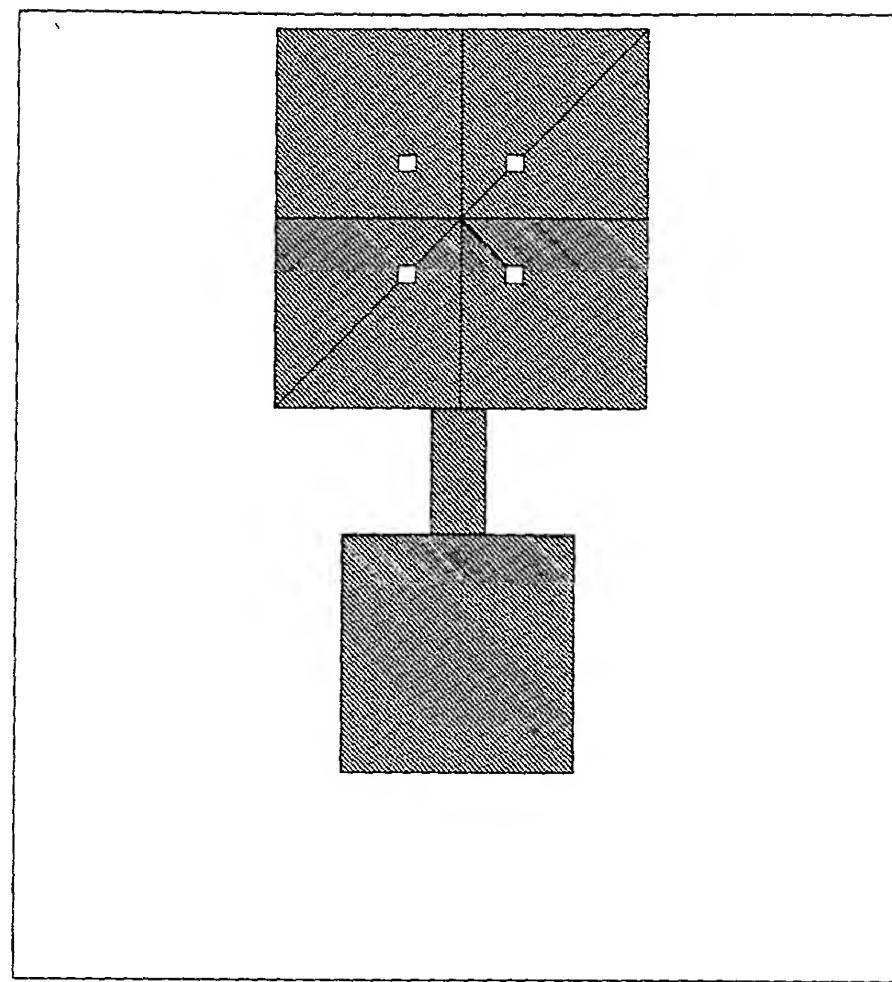


FIG. 15D

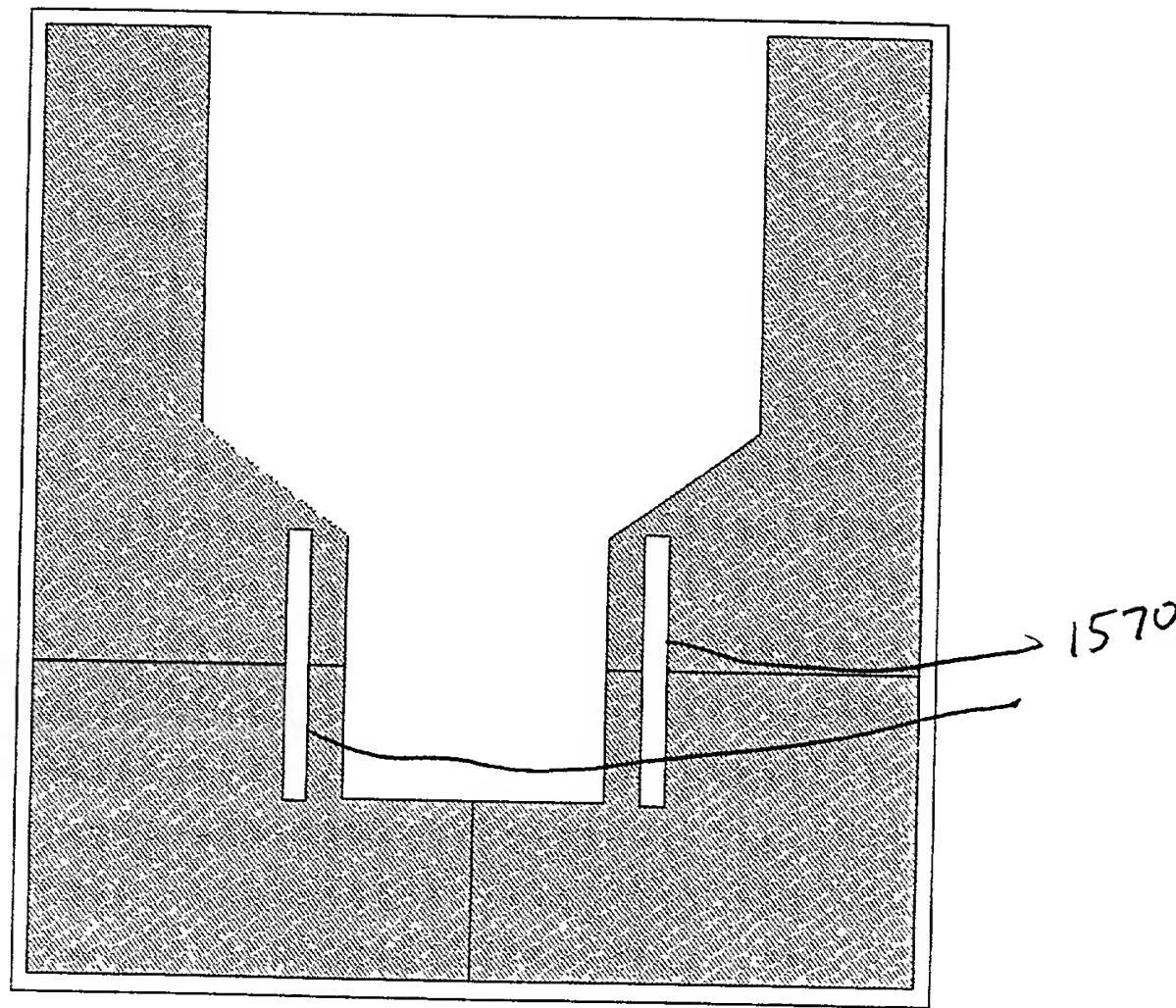


FIG. 15E

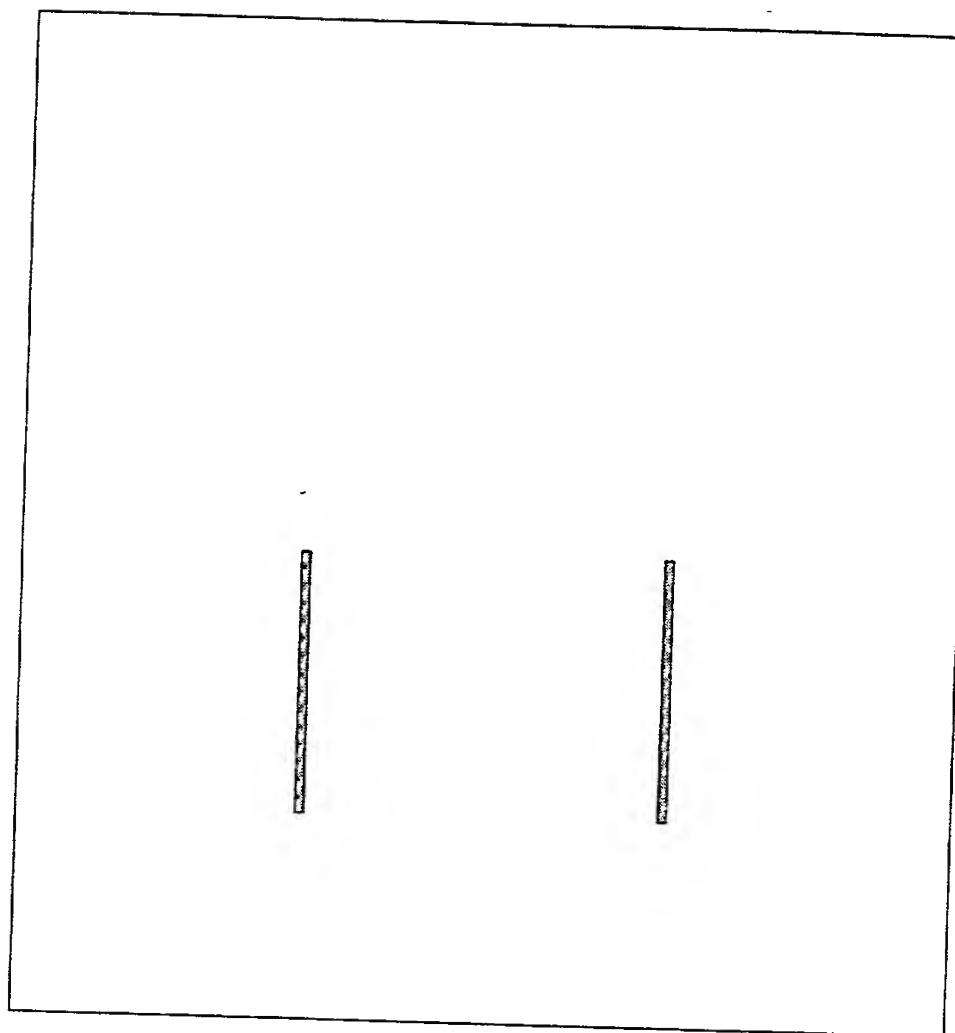


FIG. 15 F

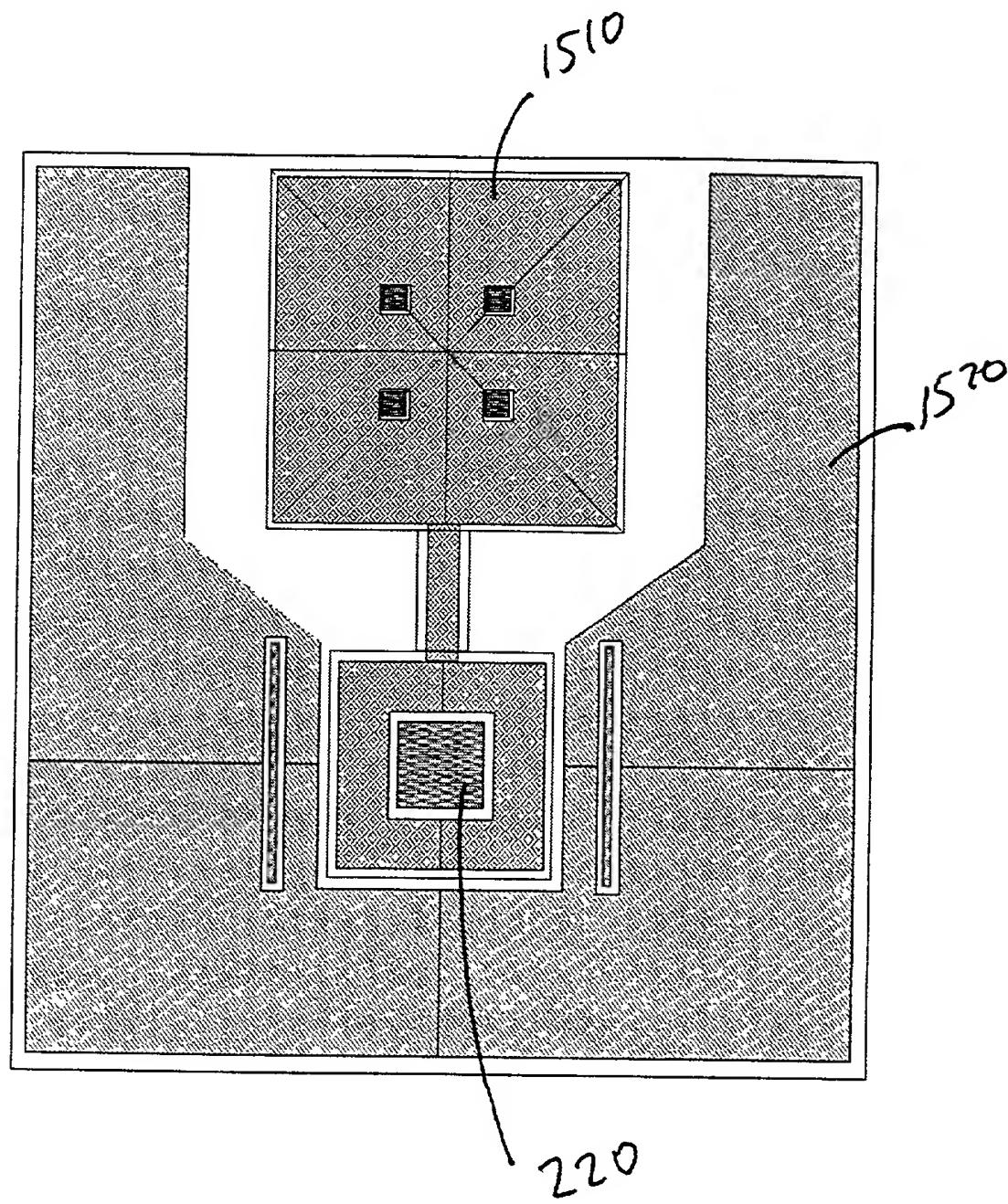


FIG. 15 G

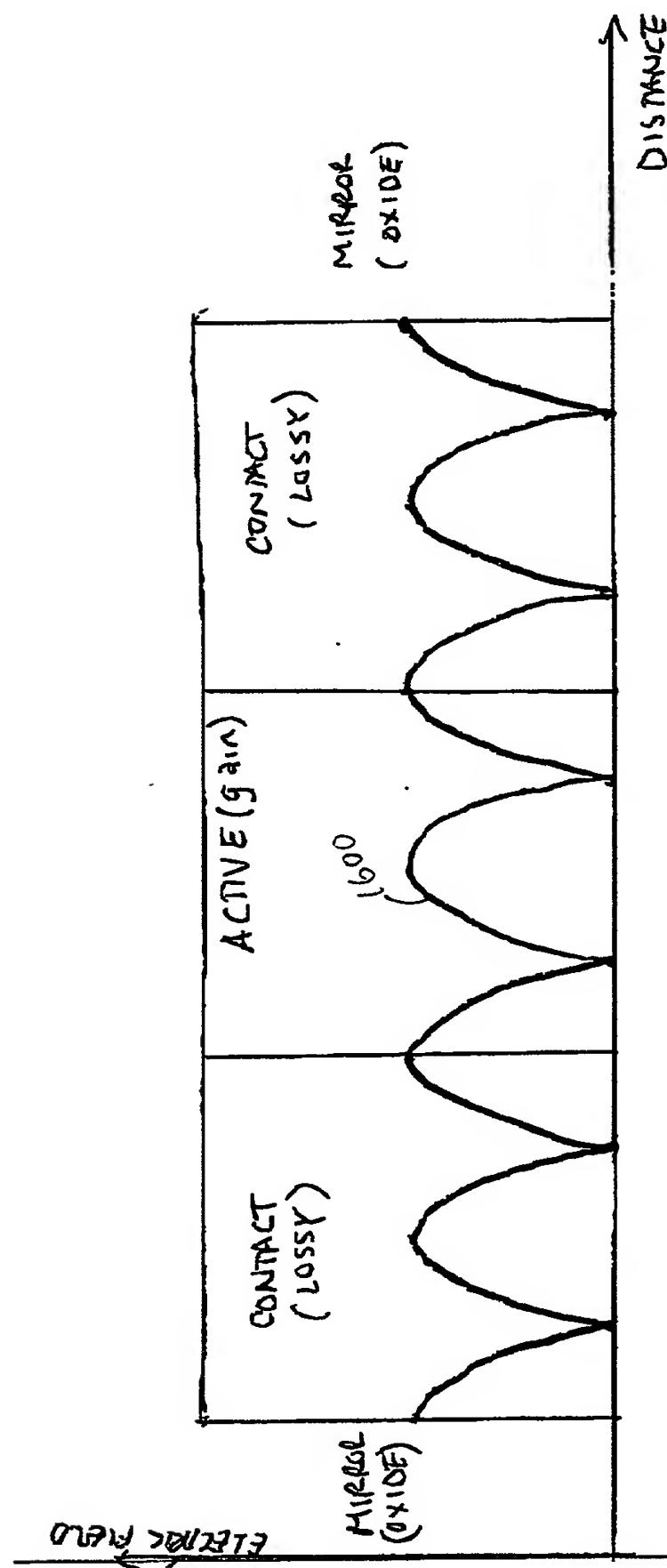
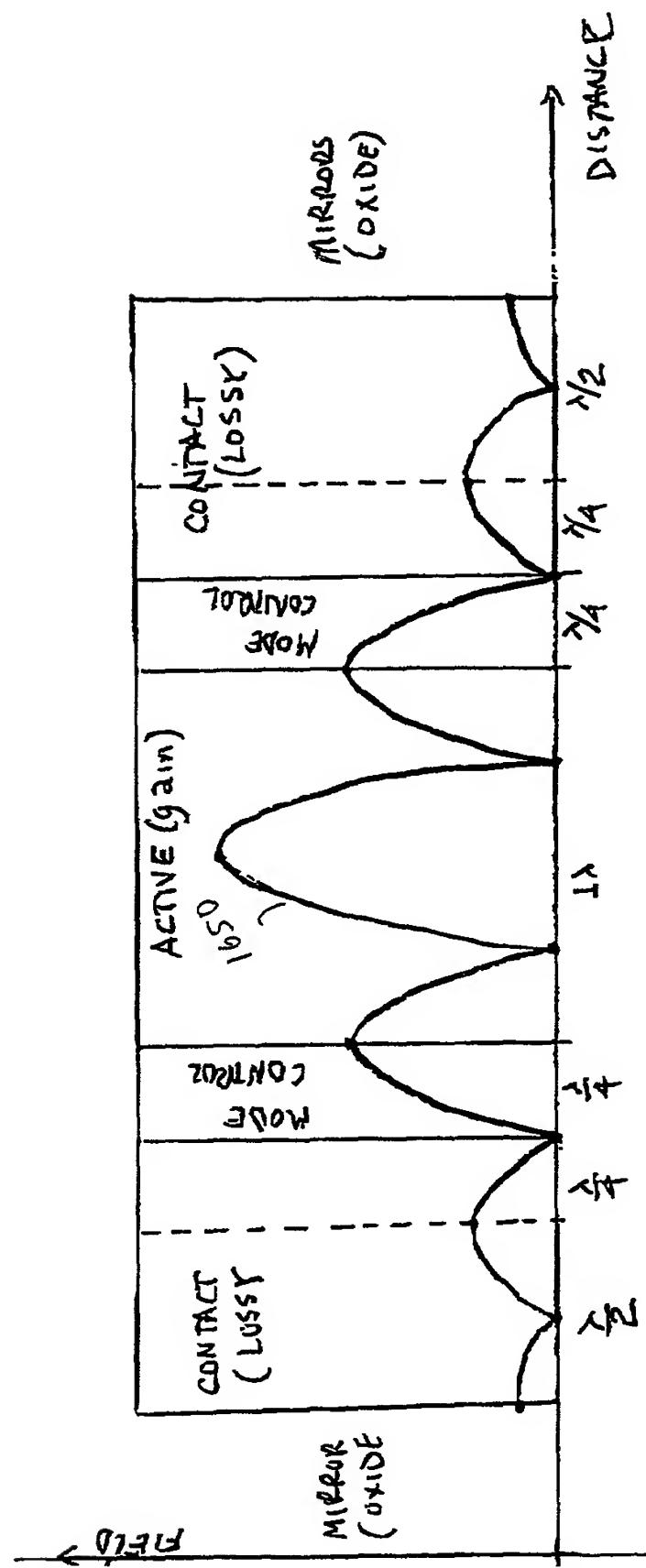


FIG. 16A



ET 6. 16 B